



PTO/SB/08a/b (08-03)
 Approved for use through 07/31/2006. OMB 0651-0031
 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE
 Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/B/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Application Number	10/768,971
				Filing Date	January 30, 2004
				First Named Inventor	Franz Hofmann
				Art Unit	N/A 2815
				Examiner Name	Not Yet Assigned <i>W/O</i>
Sheet	1	of	1	Attorney Docket Number	20046/0200815-USO

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
<i>E01</i>	AA	US-6,252,284-B1	06-26-2001	Muller et al.	

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

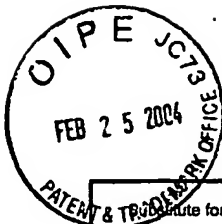
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	<i>E01</i>	Date Considered	8-25-05
--------------------	------------	-----------------	---------



PTO/SB/08a/b (08-03)
Approved for use through 07/31/2008. OMB 0651-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	10/768,971
				Filing Date	January 30, 2004
				First Named Inventor	Franz Hofmann
				Art Unit	N/A 2815
				Examiner Name	Not Yet Assigned WOS
Sheet	1	of	1	Attorney Docket Number	20046/0200815-USO

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
[Signature]	AA	US-4,996,574-B1	02-26-1991	Shirasaki	
	AB	US-5,300,455-B1	04-05-1994	Vuillermoz et al.	
	AC	US-5,623,155-B1	04-22-1997	Kerber et al.	
	AD	US-5,915,183-B1	06-22-1999	Gambino et al.	
	AE	US-6,091,076-B1	07-18-2000	Deleonibus	
[Signature]	AF	US-6,207,511-B1	03-27-2001	Chapman et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	MM-DD-YYYY			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
[Signature]	CA	Fujiwara, A. et al: "Suppression of Unintentional Formation of Parasitic SI Islands on ASI Single-Electron Transistor by the Use of Sin Masked Oxidation"; Extended Abstracts of the 1997 International Conference on Solid State Devices and Materials, Japan Society of Applied Physics, Tokyo, Japan, 1 September 1997, pages 482-483.	
	CB	Ishii, T. et al: "Characterization of One-Dimensional Conduction in an Ultra-Thin Poly-Si Wire"; Extended Abstracts of the International Conference on Solid State Devices and Materials", Japan Society of Applied Physics, Tokyo, Japan, 21 August 1995, pages 201-203.	
	CC	Hisamoto, Digh et al: "A Fully Depleted Lean-Channel Transistor (DELTA) - A Novel Vertical Ultrathin SOI MOSFET"; IEEE Electron Device Letters, Vol. 11, No. 1, January 1990, pages 36-38.	
	CD	Hisamoto, Digh et al: "A Folded-Channel MOSFET for Deep-sub-tenth Micron Era"; IEDM 98, pages 1032-1034, 1998.	
[Signature]	CE	Kedzierski, Jakub et al: "Complementary silicide source/drain thin-body MOSFETS for the 20nm gate length regime"; IEDM 2000, pages 57-60.	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	[Signature]	Date Considered	8-25-05
--------------------	-------------	-----------------	---------